subjecting the dielectric film to a wet oxidation with steam provided by heating a mixture of hydrogen and oxygen gases in a rapid thermal process chamber at a temperature greater than about 450 °C, wherein said mixture is a ratio from approximately 0.1 to approximately 0.80 of hydrogen gas to oxygen gas.

42. (Amended) A method of fabricating a semiconductor device, the method comprising:

depositing a dielectric film over a semiconductor substrate to form one of a gate and a capacitor dielectric; and

subjecting the dielectric film to a wet oxidation with steam provided by heating a mixture of hydrogen and oxygen gases in a rapid thermal process chamber at a temperature greater than about 450 °C, wherein said mixture is a ratio from approximately 0.1 to approximately 0.80 of hydrogen gas to oxygen gas.